

## **REU 2010: Investigation of Ba<sub>8</sub>Ga<sub>16</sub>Ge<sub>30</sub> Type I Clathrate by Pulsed Laser Ablation**

## Jacob Duscha, Mentors: Robert Hyde, Devajyoti Mukherjee, Sarath Witanachchi Ph.D.

#### **Abstract:**

The novel thermoelectric material Ba<sub>8</sub>Ga<sub>16</sub>Ge<sub>30</sub> type-I clathrate was investigated through the use of pulsed laser ablation. Production of particles and droplets from ablation of low density (3.87 g/cm<sup>3</sup>, 67% of theoretical) and high density targets (5.10 g/cm<sup>3</sup>, 88% of theoretical) was studied. Using a scanning electron microscope, surface morphologies were examined of ablated cold- and hot-pressed targets and films deposited on (100) Si. Laser ablated plasma plumes were analyzed using ICCD imaging establishing plasma thickness. Optical emission spectroscopy identified constituent elements in ablated plumes. Film thickness at various target-substrate distances were measured to determine deposition rates for production of thick films for future work. This investigation provides a new direction towards the growth of high quality thin films for potential TE device applications.



heavier Ba atoms trapped inside [1]

is 10.78 Å

#### **Laser-Target Interaction:**

• XRD of Ba<sub>8</sub>Ga<sub>16</sub>Ge<sub>30</sub> target (right), structure is typical of type I clathrates

• Table 1 (below): Atomic % by EDS of  $Ba_8Ga_{16}Ge_{30}$  targets. The hot-pressed target is Ga deficient and has an excess of Ge



Targets	% Ba	% Ga	% Ge	Ga/Ge
Cold-Pressed	$8.0 \pm 0.2$	$18.8 \pm 0.8$	31.1 ± 0.6	$0.6 \pm 0.0$
Hot-Pressed	$8.0 \pm 0.0$	$14.9 \pm 0.3$	$34.0 \pm 0.3$	$0.4 \pm 0.0$





Surface morphology of ablated Ba<sub>8</sub>Ga<sub>16</sub>Ge<sub>30</sub> (a) cold-pressed and (b) hotpressed targets. Targets were ablated for 100 pulses/site at a fluence of 3 J/cm<sup>2</sup>. A more complete melt zone is visible on the hot-pressed target.









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#### **Particle Reduction:**

Particles (Hot) 17 ± 1 Particles (Cold) 84 ± 10

Table 2: Particle counts for 2560 Å thick films. Particles were counted at four 850  $\mu$ m x 573  $\mu$ m locations of each film and then averaged for particle densities.





Particle defects on films produced at 4 cm target-substrate distance by (a) cold-pressed and (b) hot-pressed targets. Films produced by cold pressed targets exhibit a far greater number, as well as, larger particle defects.

#### **Thickness vs Target-Substrate Distance**



• Cold-pressed targets have more variability in film thickness per pulse due to the high concentration of particulates

decrease in film • The rapid thickness is a result of the plume expansion

• This serves as preliminary work for future investigation of thick film (>µm 5) electric transport properties

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#### **References:**

• [1] "Crystal Stuctures of Thermoelectric n- and p-type Ba<sub>8</sub>Ga<sub>16</sub>Ge<sub>30</sub>Studied by Single Crystal, Multitemperature Neutron Diffraction, Conventional X-ray Diffraction and Resonant Synchrotron X-ray Diffraction" Mogens Christensen et. Al, 11/17/2006, JACS Articles

• [2] "Growth and Characterization of Germanium-Based Type I Clathrate Thin Films Deposited by Pulsed Laser Ablation" Robert Hyde, 30th International Conference on Advanced Ceramics and Composites

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